N-Channel 30-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

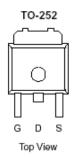
Typical Applications:

- Automotive Systems
- DC/DC Conversion Circuits
- Battery Powered Power Tools

PRODUCT SUMMARY				
VDS (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
30	2 @ V _{GS} = 10V	130		
30	$3.2 @ V_{GS} = 4.5V$	103		

in





ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage			30	V		
Gate-Source Voltage		V _{GS}	±20	v		
Continuous Drain Current ^a	T _C =25°C	I _D	130	А		
Pulsed Drain Current ^b		I _{DM}	500	A		
Continuous Source Current (Diode Conduction) ^a	T _C =25°C	I _S	56	А		
Power Dissipation ^a	T _C =25°C	PD	50	W		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient ^c	R _{θJA}	40	°C/W		
Maximum Junction-to-Case	$R_{ extsf{ heta}JC}$	3	C/ VV		

Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

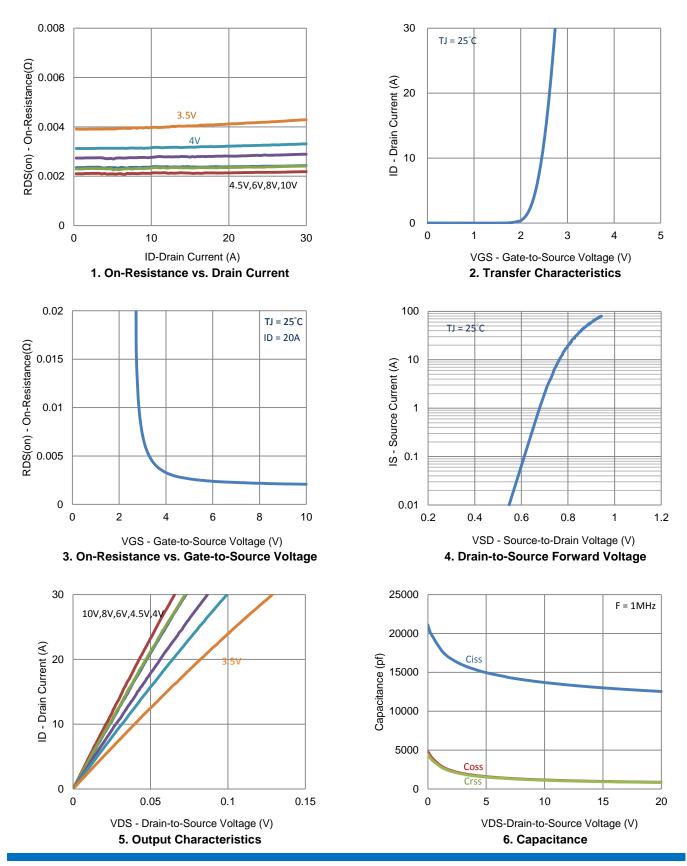
Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			±100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
	IDSS	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 V, V_{GS} = 10 V$	200			А	
	r	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 45 \text{ A}$			2	mΩ	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 44 \text{ A}$			3.2	11152	
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		22		S	
Diode Forward Voltage ^a	V _{SD}	$I_{S} = 28 \text{ A}, V_{GS} = 0 \text{ V}$		0.83		V	
		Dynamic ^b					
Total Gate Charge	Qg	V _{DS} = 15 V, V _{GS} = 4.5 V,		64		nC	
Gate-Source Charge	Q_gs	$V_{DS} = 13 V, V_{GS} = 4.5 V,$ $I_{D} = 20 A$		17			
Gate-Drain Charge	Q_gd	ID = 20 A		32			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 15 \text{ V}, \text{ R}_{L} = 0.8 \Omega,$		17			
Rise Time	t _r	$V_{DS} = 15 V, R_L - 0.8 \Omega,$ $I_D = 20 A,$		28		20	
Turn-Off Delay Time	t _{d(off)}	$V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$		168		ns	
Fall Time	t _f	$V_{\text{GEN}} = 10$ V, $V_{\text{GEN}} = 0.22$		65			
Input Capacitance	C _{iss}			13001			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ Mhz}$		966		рF	
Reverse Transfer Capacitance	C _{rss}			939			

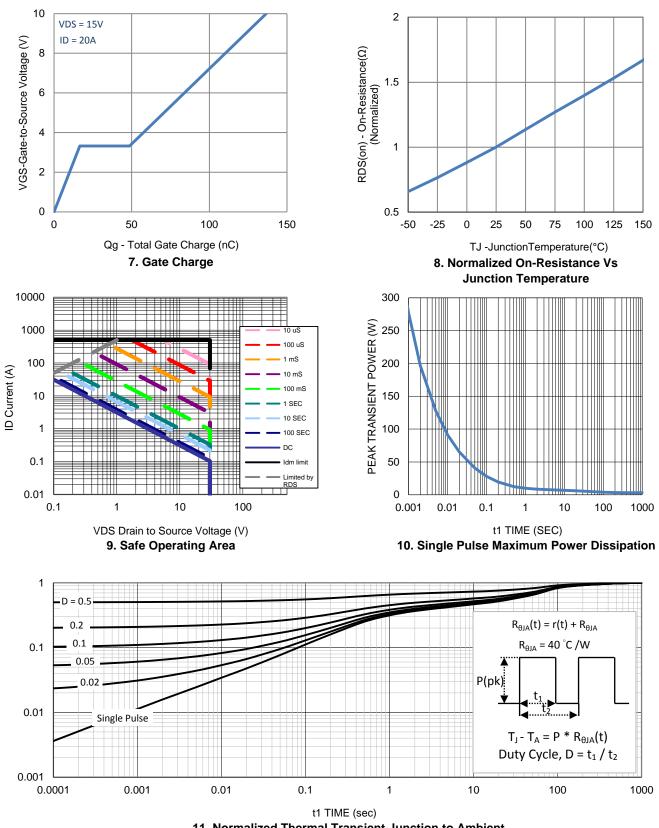
Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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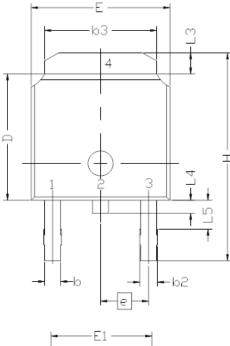
Typical Electrical Characteristics

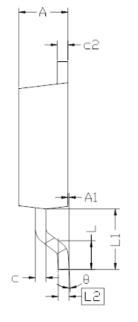


Typical Electrical Characteristics

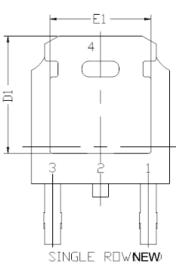
11. Normalized Thermal Transient Junction to Ambient

Package Information





	DIMENS:	IONAL F	REQMIS			
SYMBOL	MIN	NDM	MAX			
E	6.40	6.60	6.731			
L	1.40	1.52	1.77			
L1	2	.743 R	ĒF			
L2	0.508 BSC					
L3	0.89		1.27			
L4	0.64		1.01			
L5						
D	6.00	6.10	6,223			
Н	9.40	10.00	10.40			
b	0.64	0.76	0.88			
b2	0.77	0.84	1.14			
b3	5.21	5.34	5.46			
e	2.	286 BS	C			
I A	2.20	2.30	2.38			
A1	0		0.127			
C	0.45	0.50	0.60			
2 	0.45	0.50	0,58			
D1	5.30					
E1	4.40					
θ	0*		10°			



Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.